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AMENDMENTS TO THE CLAIMS:

If entered, this listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A method of self-calibrating and testing the vaporized flow of a liquid precursor in a thin film vaporization system comprising the steps of:

providing a thin film vaporization system comprising stored liquid precursors in tanks under pressure connected to a deposition chamber via a manifold which in turn is connected to pipe lines emanating from each tank and coupled to own liquid flow meters (LFMs) and injection valves (IVs);

activating a servo mechanism to pump down said deposition chamber to achieve partial vacuum therein;

opening a downstream throttle valve (TV) for a carrier gas to flow through said manifold to commence self-calibration wherein said carrier gas is a second helium;

a first timing to monitor a baseline self-calibrated pressure by a pre-determined TV opening which correlates with the specified baseline pressure in said deposition chamber;

a second timing to allow for the stabilization of carrier gas after throttling said TV to a predetermined opening;

selecting a liquid precursor and its own said respective pipe line with said own LFM and own IV connected to said deposition chamber via said manifold;

setting said own IV to a predetermined opening to start said liquid precursor to flow;

setting said TV opening to a normal liquid precursor flow rate for film deposition;

a third timing to allow for liquid precursor flow to stabilize;

a fourth timing to allow vaporization of said liquid precursor in said deposition chamber;

measuring final pressure in said deposition chamber;

stopping the flow of said precursor fluid; and

pumping down said deposition chamber to continue with said film deposition pending the result of said pressure rise.

- 2. (Original) The method according to claim 1, wherein said tanks are pressurized by helium gas.
- 3. (Original) The method according to claim 2, wherein said helium gas is pressurized to between about 20 to 30 pounds per square inch gauge (psig).
- 4. (Original) The method according to claim 1, wherein said helium gas is kept at room temperature.
- 5. (Original) The method according to claim 1, wherein said manifold has heater elements.
- 6. (Original) The method according to claim 5, wherein said heated fixture elements are spaced nominally at 290

TS-00-903 mils between about 250 to 350 mils from distribution shower head.

7. (Original) The method according to claim 5, wherein said heated fixture is heated nominally to 400 °C between about 350 to 450 °C.

8. (Canceled)

- 9. (Amended) The method according to claim 1, wherein said flow of said second helium through said manifold is between about 750 to 850 milligrams per minute (mgm).
- 10. (Original) The method according to claim 1, wherein said first timing is between about 5 to 15 seconds.
- 11. (Original) The method according to claim 1, wherein said baseline self-calibrated pressure is between about 2 to 4 torr.
- 12. (Original) The method according to claim 1, wherein said second timing is between about 4 to 6 seconds.

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- 13. (Original) The method according to claim 1, wherein said liquid precursor is tetraethylorthosilicate (TEOS).
- 14. (Original) The method according to claim 1, wherein said liquid precursor is triethylborate (TEB).
- 15. (Original) The method according to claim 1, wherein said liquid precursor is tri-ethylphosphate (TEPO).
- 16. (Original) The method according to claim 1, wherein said injection valve (IV) comprises a venturi tube.
- 17. (Amended) The method according to claim 1, wherein said normal liquid precursor flow rate is between about 800 to 1000 milli gram milligram per minute (mgm).
- 18. (Original) The method according to claim 1, wherein said third timing to allow for liquid precursor to stabilize is between about 7 to 9 seconds.
- 19. (Original) The method according to claim 1, wherein said fourth timing to allow for liquid precursor vaporized flow to be verified is between about 4 to 6 seconds.

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- 20. (Original) The method according to claim 1, wherein said final pressure in said deposition chamber is between about 6.5 and 7.5 torr.
- 21. (Original) The method according to claim 1, wherein said pumping down said deposition chamber is accomplished within between about 9 to 11 seconds.

22 - 31. (Canceled)